Jiadi Zhu

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	A comprehensive review on emerging artificial neuromorphic devices. Applied Physics Reviews, 2020, 7,	11.3	417
2	lon Gated Synaptic Transistors Based on 2D van der Waals Crystals with Tunable Diffusive Dynamics. Advanced Materials, 2018, 30, e1800195.	21.0	368
3	Brain-inspired computing with memristors: Challenges in devices, circuits, and systems. Applied Physics Reviews, 2020, 7, .	11.3	217
4	Dual-Gated MoS ₂ Neuristor for Neuromorphic Computing. ACS Applied Materials & Interfaces, 2019, 11, 41482-41489.	8.0	78
5	Designing artificial two-dimensional landscapes via atomic-layer substitution. Proceedings of the National Academy of Sciences of the United States of America, 2021, 118, .	7.1	43
6	Vertical WS2/SnS2 van der Waals Heterostructure for Tunneling Transistors. Scientific Reports, 2018, 8, 17755.	3.3	40
7	A Novel Tunnel FET Design Through Adaptive Bandgap Engineering With Constant Sub-Threshold Slope Over 5 Decades of Current and High \$ext{I}_{mathrm {ON}}/ext{I}_{mathrm {OFF}} Ratio. IEEE Electron Device Letters, 2017, 38, 540-543.	3.9	39
8	Stochastic neuron based on IGZO Schottky diodes for neuromorphic computing. APL Materials, 2019, 7,	5.1	35
9	Design and Simulation of a Novel Graded-Channel Heterojunction Tunnel FET With High \${I} _{scriptscriptstyleext {ON}}/{I} _{scriptscriptstyleext {OFF}}\$ Ratio and Steep Swing. IEEE Electron Device Letters, 2017, 38, 1200-1203.	3.9	28
10	Physically Transient True Random Number Generators Based on Paired Threshold Switches Enabling Monte Carlo Method Applications. IEEE Electron Device Letters, 2019, 40, 1096-1099.	3.9	26
11	Soft-lock drawing of super-aligned carbon nanotube bundles for nanometre electrical contacts. Nature Nanotechnology, 2022, 17, 278-284.	31.5	24
12	Neuromorphic Computing: Ion Gated Synaptic Transistors Based on 2D van der Waals Crystals with Tunable Diffusive Dynamics (Adv. Mater. 21/2018). Advanced Materials, 2018, 30, 1870149.	21.0	20
13	Bipolar to unipolar mode transition and imitation of metaplasticity in oxide based memristors with enhanced ionic conductivity. Journal of Applied Physics, 2018, 124, .	2.5	19
14	Interfacial redox processes in memristive devices based on valence change and electrochemical metallization. Faraday Discussions, 2019, 213, 41-52.	3.2	18
15	New Understanding of Random Telegraph Noise Amplitude in Tunnel FETs. IEEE Transactions on Electron Devices, 2017, 64, 3324-3330.	3.0	11
16	Combinational Access Tunnel FET SRAM for Ultra-Low Power Applications. , 2018, , .		10
17	New Insights Into Energy Efficiency of Tunnel FET With Awareness of Source Doping Gradient Variation. IEEE Transactions on Electron Devices, 2018, 65, 2003-2009.	3.0	6
18	Voltage-Controlled Magnetoresistance in Silicon Nanowire Transistors. Scientific Reports, 2018, 8, 15194.	3.3	6

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19	Highly Uniform Twoâ€Terminal Artificial Synapses Based on Polycrystalline Hf 0.5 Zr 0.5 O 2 for Sparsified Back Propagation Networks. Advanced Electronic Materials, 2020, 6, 2000204.	5.1	4
20	Deep insights into dielectric breakdown in tunnel FETs with awareness of reliability and performance co-optimization. , 2016, , .		2
21	Resistive switching and synaptic plasticity in HfO <inf>2</inf> -based memristors with single-layer and bilayer structures. , 2018, , .		2
22	Benchmarking of multi-finger Schottky-Barrier tunnel FET for ultra-low power applications. , 2018, , .		0
23	Conductance quantization in oxide-based resistive switching devices. , 2019, , .		0